

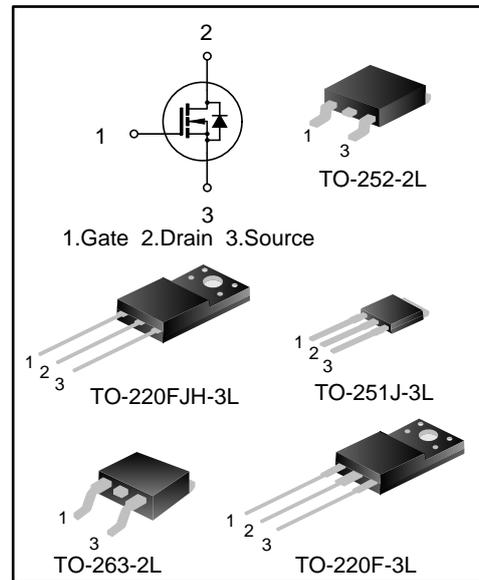
11A, 700V SUPER JUNCTION MOS POWER TRANSISTOR

DESCRIPTION

SVSP11N70F/FJH/D/MJ/SD2 is an N-channel enhancement mode high voltage power MOSFETs produced using Silan's super junction MOS technology. It achieves low conduction loss and switching losses. It leads the design engineers to their power converters with high efficiency, high power density, and superior thermal behavior. Furthermore, it's universal applicable, for example, it is suitable for hard and soft switching topologies.

FEATURES

- ◆ 11A, 700V, $R_{DS(on)(typ.)}=0.37\Omega@V_{GS}=10V$
- ◆ New revolutionary high voltage technology
- ◆ Ultra low gate charge
- ◆ Enhanced avalanche capability
- ◆ Extreme dv/dt rated
- ◆ High peak current capability



ORDERING INFORMATION

Part No.	Package	Marking	Hazardous substance control	Packing Type
SVSP11N70FD2	TO-220F-3L	P11N70FD2	Halogen free	Tube
SVSP11N70FJHD2	TO-220FJH-3L	P11N70FJH	Halogen free	Tube
SVSP11N70DD2TR	TO-252-2L	P11N70D	Halogen free	Tape & Reel
SVSP11N70MJD2	TO-251J-3L	P11N70MJD2	Halogen free	Tube
SVSP11N70SD2	TO-263-2L	P11N70SD2	Halogen free	Tube



ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted, T_C=25°C)

Characteristics	Symbol	Ratings			Unit
		SVSP11N70 FD2/FJHD2	SVSP11N70 DD2/MJD2	SVSP11N70 SD2	
Drain-Source Voltage	V _{DS}	700			V
Gate-Source Voltage	V _{GS}	±30			V
Drain Current	I _D	T _C =25°C			A
		T _C =100°C			
Drain Current Pulsed	I _{DM}	44			A
Power Dissipation (T _C =25°C) - Derate above 25°C	P _D	37	130	139	W
		0.3	1.0	1.1	W/°C
Single Pulsed Avalanche Energy (Note 1)	E _{AS}	576			mJ
Reverse diode dv/dt (Note 2)	dv/dt	15			V/ns
MOSFET dv/dt ruggedness (Note 3)	dv/dt	50			V/ns
Operation Junction Temperature Range	T _J	-55~+150			°C
Storage Temperature Range	T _{stg}	-55~+150			°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Ratings			Unit
		SVSP11N70 FD2/FJHD2	SVSP11N70 DD2/MJD2	SVSP11N70 SD2	
Thermal Resistance, Junction-to-Case	R _{θJC}	3.4	0.96	0.9	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	62.5	62.5	°C/W

ELECTRICAL CHARACTERISTICS (Unless otherwise noted, T_c=25°C)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	700	--	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =700V, V _{GS} =0V	--	--	1.0	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	2.0	--	4.0	V
Static Drain- Source on State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5.5A	--	0.37	0.42	Ω
Gate resistance	R _g	f=1.0MHz	--	4.7	--	Ω
Input Capacitance	C _{iss}	f=1MHz, V _{GS} =0V, V _{DS} =100V	--	673	--	pF
Output Capacitance	C _{oss}		--	37	--	
Reverse Transfer Capacitance	C _{rss}		--	2.3	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} =350V, V _{GS} =10V, R _G =24Ω, I _D =11A (Note 4,5)	--	14	--	ns
Turn-on Rise Time	t _r		--	37	--	
Turn-off Delay Time	t _{d(off)}		--	70	--	
Turn-off Fall Time	t _f		--	33	--	
Total Gate Charge	Q _g	V _{DD} =560V, V _{GS} =10V, I _D =11A (Note 4,5)	--	24	--	nC
Gate-Source Charge	Q _{gs}		--	5.2	--	
Gate-Drain Charge	Q _{gd}		--	12	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I _S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	11	A
Pulsed Source Current	I _{SM}		--	--	44	
Diode Forward Voltage	V _{SD}	I _S =11A, V _{GS} =0V	--	--	1.4	V
Reverse Recovery Time	T _{rr}	I _S =11A, V _{GS} =0V, dI _F /dt=100A/μs (Note 4)	--	374	--	ns
Reverse Recovery Charge	Q _{rr}		--	3.9	--	μC

Notes:

- L=79mH, I_{AS}=3.5A, V_{DD}=100V, R_G=25Ω, starting T_J=25°C;
- V_{DS}=0~400V, I_{SD}≤11A, T_J=25°C;
- V_{DS}=0~480V;
- Pulse Test: Pulse width ≤300μs, Duty cycles≤2%;
- Essentially independent of operating temperature.



TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

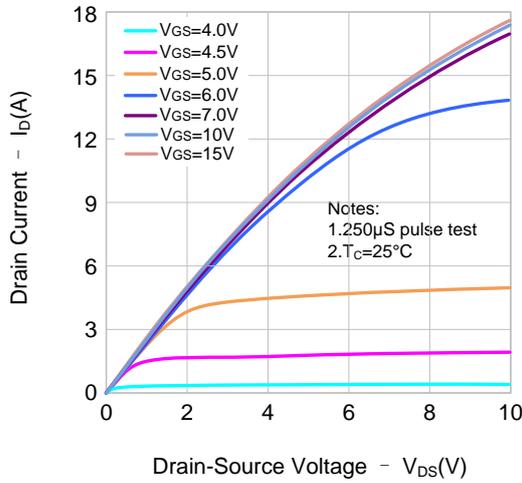


Figure 2. Transfer Characteristics

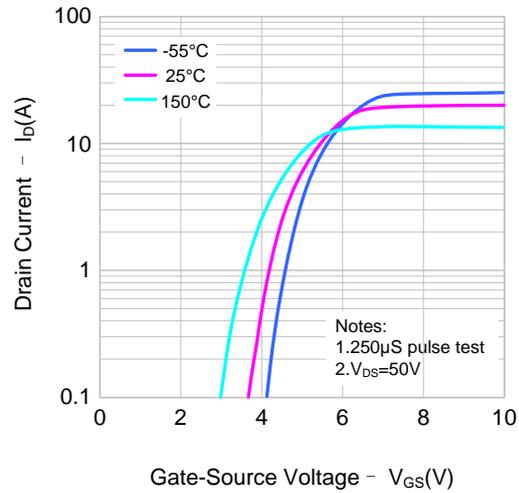


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

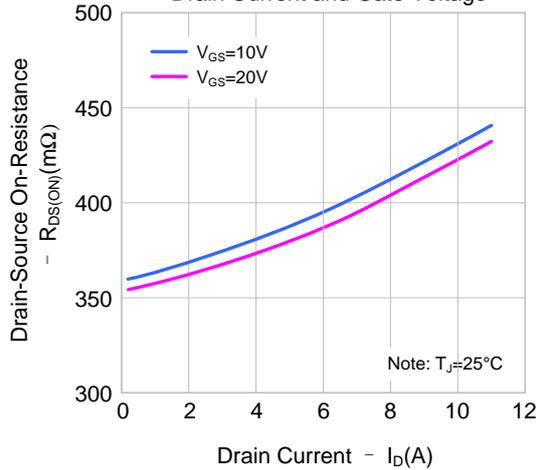


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

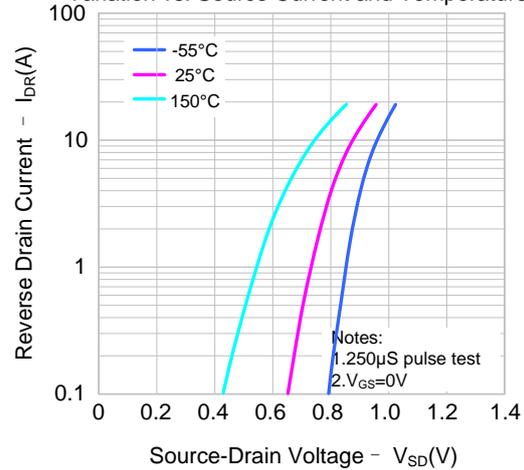


Figure 5. Capacitance Characteristics

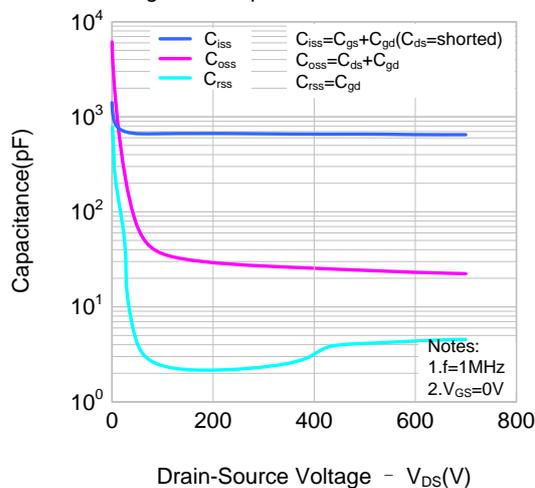
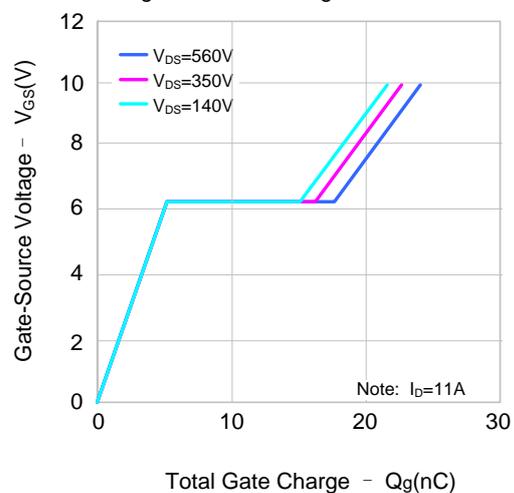


Figure 6. Gate Charge Characteristics





TYPICAL CHARACTERISTICS (continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

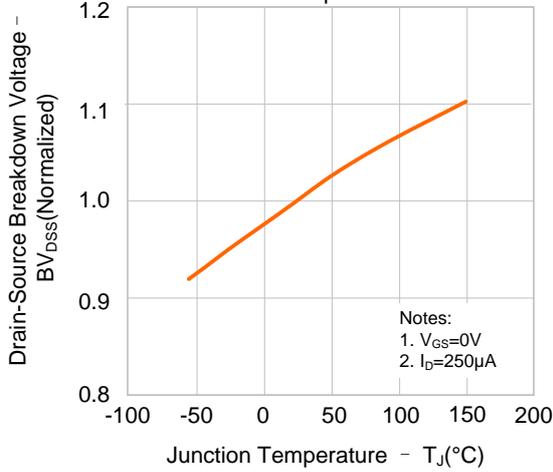


Figure 8. On-resistance Variation vs. Temperature

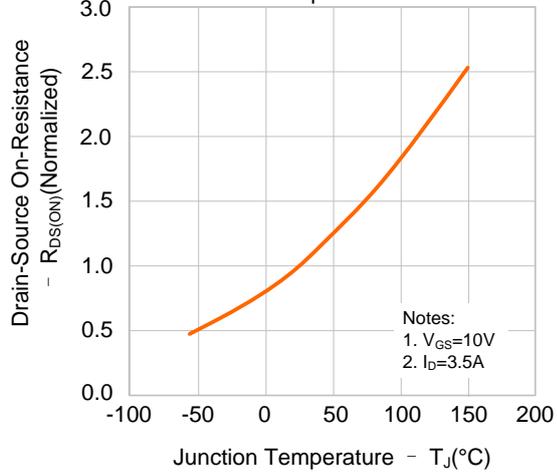


Figure 9-1. Max. Safe Operating Area (SVSP11N70F/FJHD2)

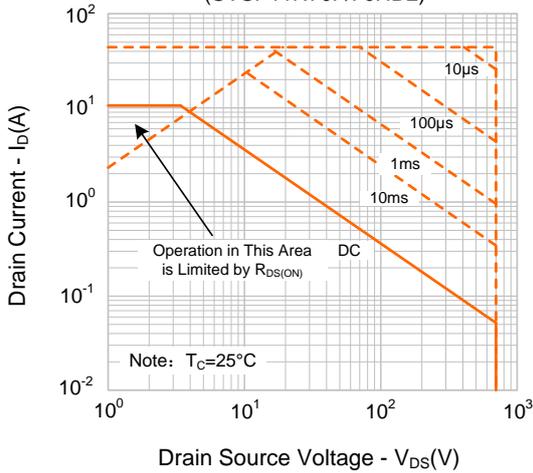


Figure 9-2. Max. Safe Operating Area (SVSP11N70D/MJD2)

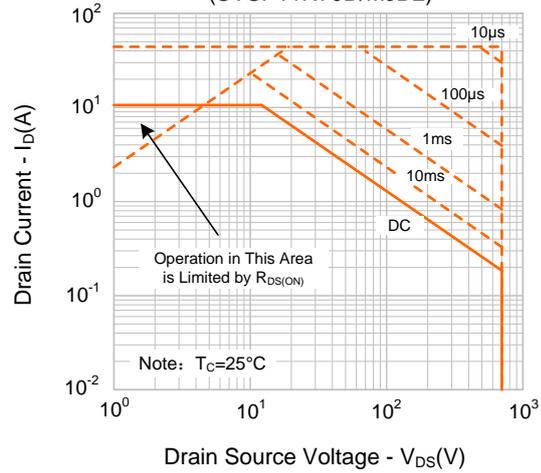
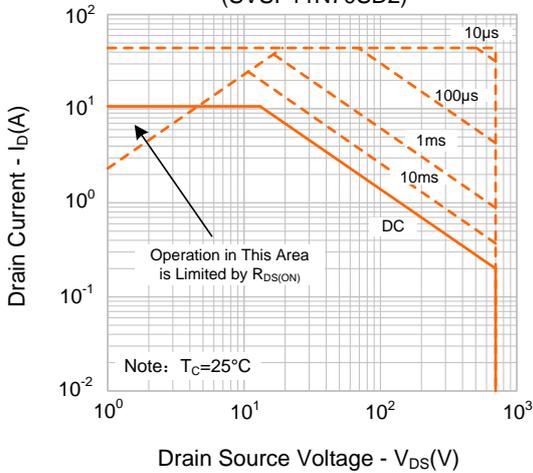


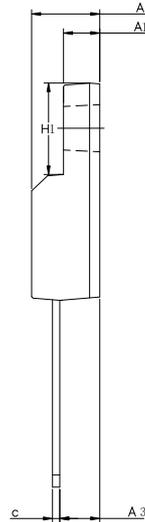
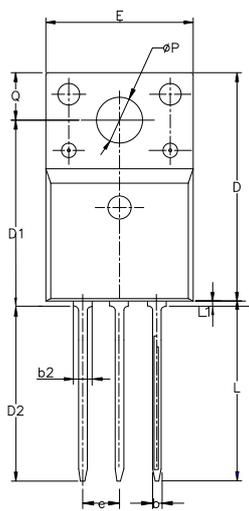
Figure 9-3. Max. Safe Operating Area (SVSP11N70SD2)



PACKAGE OUTLINE

TO-220FJH-3L

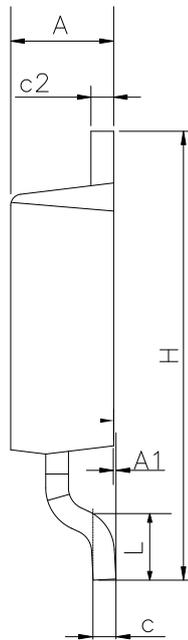
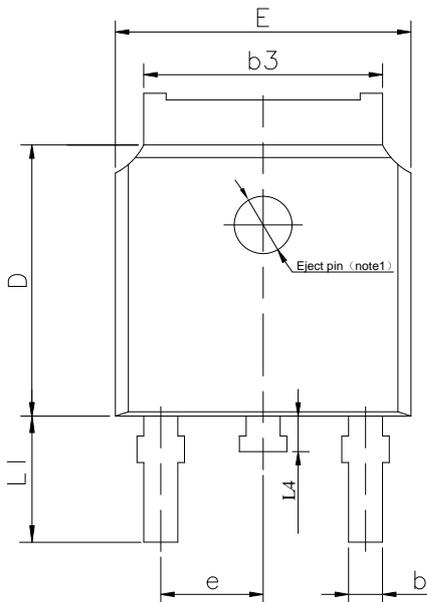
Unit: mm



SYMBOL	MIN	NOM	MAX
A	4.42	4.70	5.02
A1	2.30	2.54	2.80
A3	2.50	2.76	3.10
b	0.55	0.70	0.80
b2	—	—	1.29
c	0.35	0.50	0.65
D	15.25	15.87	16.25
D1	12.87	13.07	13.27
D2	12.28	12.48	12.68
E	9.73	10.16	10.36
e	2.54BCS		
H1	6.40	6.68	7.00
L	12.48	12.98	13.48
L1	—	—	0.85
φP	3.00	3.18	3.40
Q	3.05	3.30	3.55

TO-252-2L

Unit: mm



SYMBOL	MIN	NOM	MAX
A	2.10	2.30	2.50
A1	0	---	0.127
b	0.66	0.76	0.89
b3	5.10	5.33	5.46
c	0.45	---	0.65
c2	0.45	---	0.65
D	5.80	6.10	6.40
E	6.30	6.60	6.90
e	2.30TYP		
H	9.60	10.10	10.60
L	1.40	1.50	1.70
L1	2.90REF		
L4	0.60	0.80	1.00

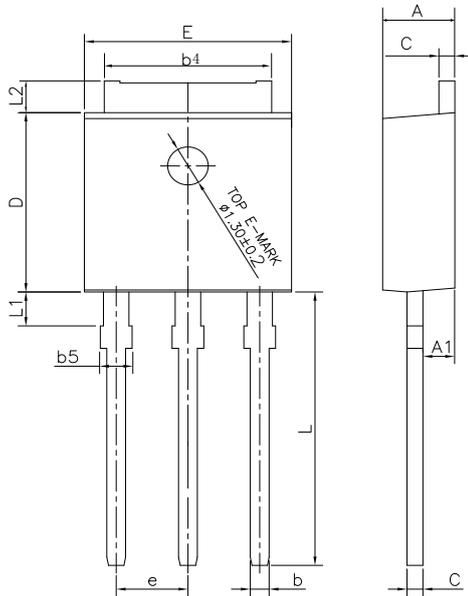
NOTE1 : There are two conditions for this position:has an eject pin or has no eject pin.



PACKAGE OUTLINE(continued)

TO-251J-3L

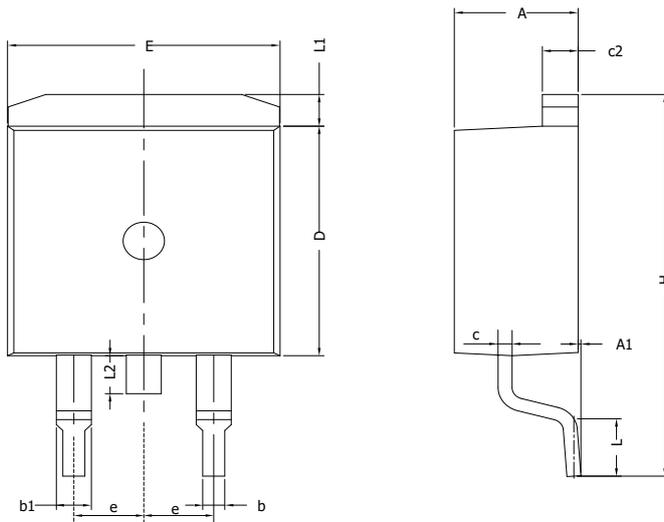
Unit: mm



SYMBOL	MIN	NOM	MAX
A	2.18	2.30	2.39
A1	0.89	1.00	1.14
b	0.56	---	0.89
b4	4.95	5.33	5.46
b5	---	---	1.05
c	0.46	---	0.61
D	5.97	6.10	6.27
E	6.35	6.60	6.73
e	2.29 BCS		
L	8.89	9.30	9.65
L1	0.95	---	1.50
L2	0.89	---	1.27

TO-263-2L

Unit: mm



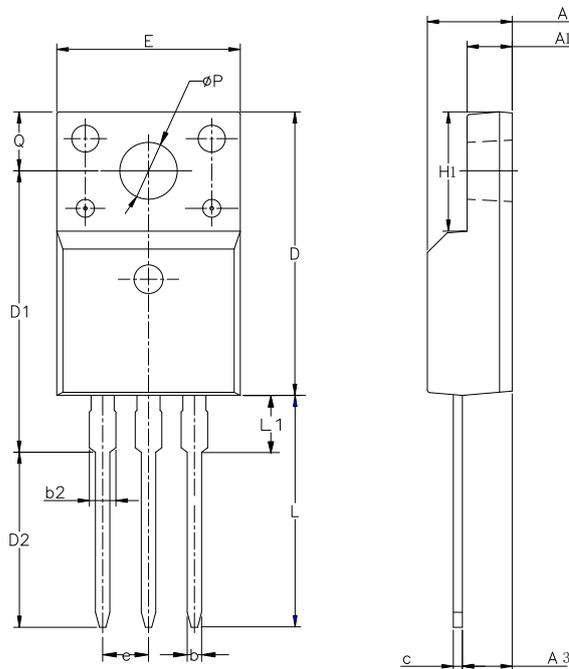
SYMBOL	MIN	NOM	MAX
A	4.30	4.57	4.72
A1	0	0.10	0.25
b	0.71	0.81	0.91
c	0.30	---	0.60
c2	1.17	1.27	1.37
D	8.50	---	9.35
E	9.80	---	10.45
e	2.54BSC		
H	14.70	---	15.75
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	---	---	1.75



PACKAGE OUTLINE(continued)

TO-220F-3L

Unit: mm



SYMBOL	MIN	NOM	MAX
A	4.42	4.70	5.02
A1	2.30	2.54	2.80
A3	2.50	2.76	3.10
b	0.70	0.80	0.90
b2	—	—	1.47
c	0.35	0.50	0.65
D	15.25	15.87	16.25
D1	15.30	15.75	16.30
D2	9.30	9.80	10.30
E	9.73	10.16	10.36
e	2.54BSC		
H1	6.40	6.68	7.00
L	12.48	12.98	13.48
L1	/	/	3.50
ϕP	3.00	3.18	3.40
Q	3.05	3.30	3.55

Important notice :

- The instructions are subject to change without notice! Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current.
- Our products are consumer electronic products, and / or civil electronic products.
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Part No.: SVSP11N70F/FJH/D/MJ/SD2 Document Type: Datasheet
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Rev.: 1.1

Revision History:

1. Modify the Electrical schematic and TYPICAL TEST CIRCUIT
 2. Delete NOMENCLATURE
-

Rev.: 1.0

Revision History:

1. First release
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